AMENDMENTS TO THE CLAIMS

Please **CANCEL** claims 18, 30 and 33-35 without prejudice or disclaimer.

Please **ADD** claims 36-45 as shown below.

The following is a complete list of all claims in this application.

1-35. (Cancelled)

36. (New) An apparatus for manufacturing a liquid crystal device, comprising:

a first chamber receiving a substrate; and

a second chamber forming a gate insulating layer, an amorphous silicon layer and a doped amorphous silicon layer on the substrate; and

a third chamber forming a metal layer on the doped amorphous silicon layer,

wherein the apparatus sequentially forms the gate insulating layer, the amorphous silicon layer, the doped amorphous silicon layer and the metal layer without breaking a vacuum.

37. (New) The apparatus of claim 36, further comprising a preheat chamber receiving the substrate from the first chamber and preheating the substrate.

38. (New) The apparatus of claim 37, wherein the first chamber, the preheat chamber, the second chamber and the third chamber are arranged in series.

39. (New) The apparatus of claim 36, wherein the first chamber receives the substrate having a gate line formed thereon.

40. (New) The apparatus of claim 36, wherein the second chamber is a chemical vapor deposition (CVD) chamber.

41. (New) The apparatus of claim 36, wherein the third chamber is a sputtering chamber.

42. (New) The apparatus of claim 36, wherein the second chamber comprises:

a first deposition chamber forming the gate insulating layer and an amorphous silicon layer; and

a second deposition chamber forming the doped amorphous silicon layer.

43. (New) The apparatus of claim 42, wherein the first deposition chamber and the second deposition chamber are chemical vapor deposition (CVD) chambers.

44. (New) The apparatus of claim 36, wherein the metal layer is chromium.

45. (New) The apparatus of claim 36, wherein the gate insulating layer is formed at a thickness between 3000 Å to 6000 Å, the amorphous silicon layer is formed at a thickness between 1000 Å to 3000 Å, and the doped amorphous silicon layer is formed at a thickness of 200 Å to 1000 Å.